

1SS388

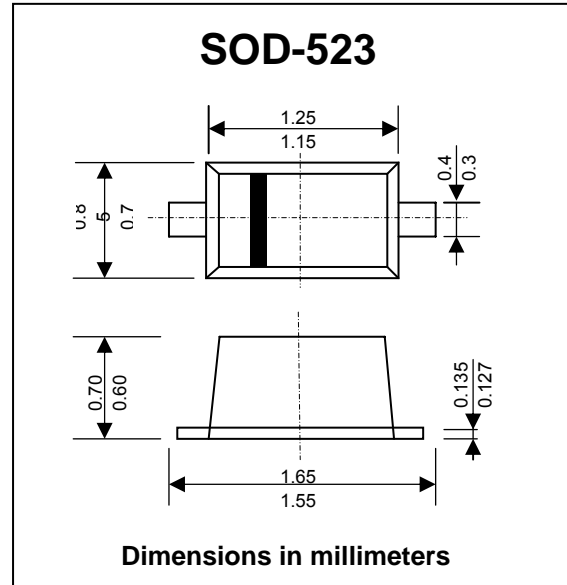
SILICON EPITAXIAL SCHOTTKY BARRIER DIODE

FEATURES :

- * Small package
- * Low forward voltage
- * Low reverse current
- * Pb / RoHS Free

MECHANICAL DATA :

- * Lead Finish : 100% Matte Sn (Tin)
- * Mounting Position : Any
- * Qualified Max Reflow Temperature : 260 °C



Absolute Maximum Ratings (Ta = 25 °C)

Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	V_{RM}	45	V
Maximum Reverse Voltage	V_R	40	V
Maximum Average Forward Current	I_F	100	mA
Maximum Peak Forward Current	I_{FM}	300	mA
Maximum Surge Current (10 ms)	I_{FSM}	1.0	A
Power Dissipation	P_{tot}	150	mW
Junction Temperature	T_J	125	°C
Storage Temperature Range	T_{STG}	-55 to + 125	°C

Electrical Characteristics (Ta = 25 °C)

Parameter	Symbol	Test Condition	Max.	Unit
Forward Voltage	V_F	$I_F = 50 \text{ mA}$	0.6	V
Reverse Current	I_R	$V_R = 10 \text{ V}$	5	μA
Total Capacitance	C_T	$f = 1 \text{ MHz}$	25	pF

RATING AND CHARACTERISTIC CURVES (1SS388)

FIG.1 - POWER DISSIPATION VS. AMBIENT TEMPERATURE

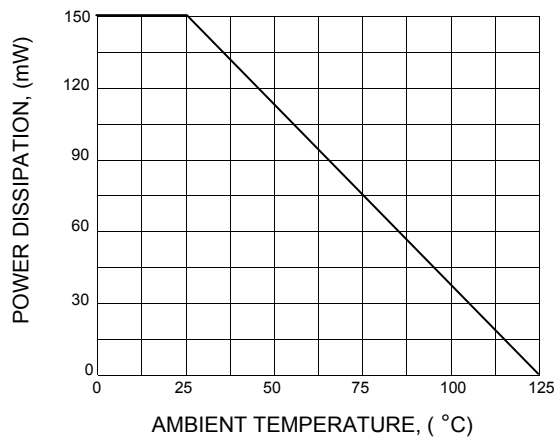


FIG.2 - TOTAL CAPACITANCE VS. REVERSE VOLTAGE

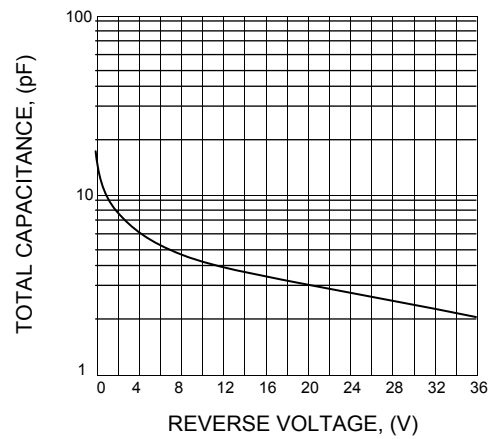


FIG.3 - TYPICAL FORWARD CHARACTERISTICS

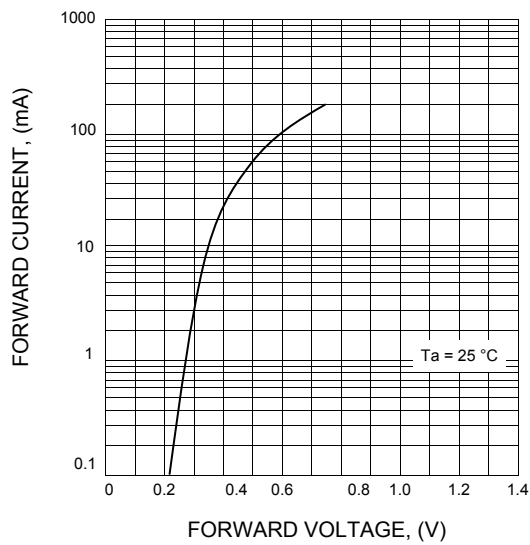


FIG.4 - TYPICAL REVERSE CHARACTERISTICS

